

CM600HN-5F

HIGH POWER SWITCHING USE
INSULATED TYPE

CM600HN-5F



- Ic 600A
- VCES 250V
- Insulated Type
- 1-element in a pack
- UL Recognized

Yellow Card No. E80276

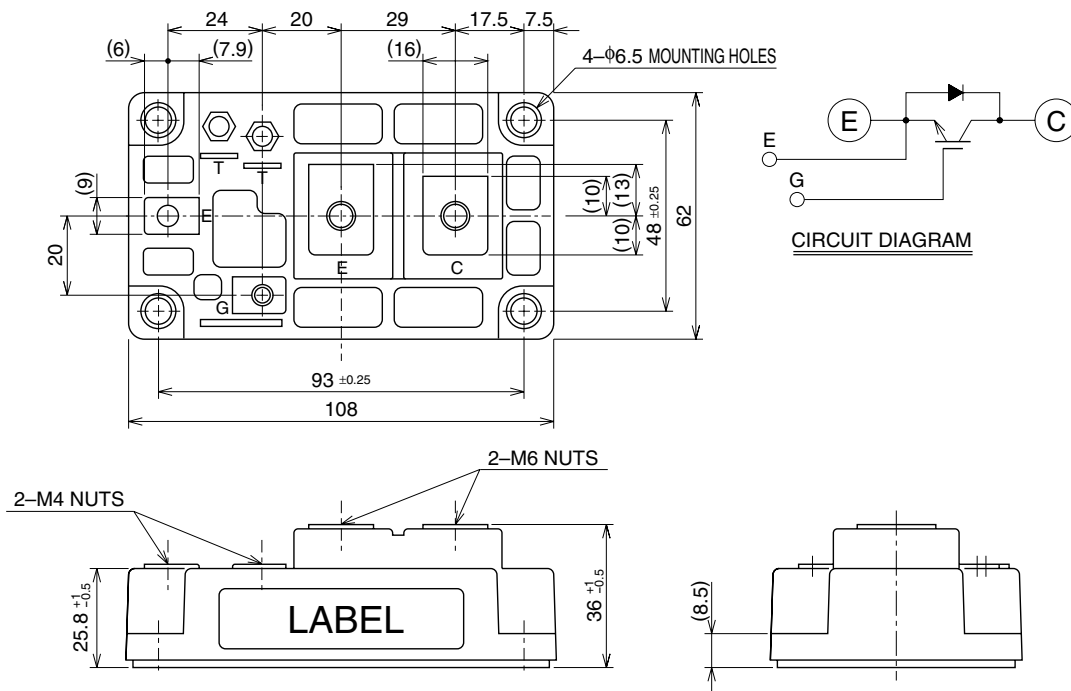
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APPLICATION

UPS, Forklift

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS (T_j = 25°C, unless otherwise specified)

Symbol	Item	Conditions	Ratings	Unit
V _{CE} S	Collector-emitter voltage	G-E Short	250	V
V _{GE} S	Gate-emitter voltage	C-E Short	±20	V
I _C	Collector current	T _c = 25°C	600	A
I _{CM}		Pulse (Note 2)	1200	A
I _E (Note 1)	Emitter current	T _c = 25°C	600	A
I _{EM} (Note 1)		Pulse (Note 2)	1200	A
P _C (Note 3)	Maximum collector dissipation	T _c = 25°C	1780	W
T _j	Junction temperature	—	-40 ~ +150	°C
T _{stg}	Storage temperature	—	-40 ~ +125	°C
V _{iso}	Isolation voltage	Charged part to base plate, sinusoidal, AC 60Hz 1min.	2500	V _{rms}
—	Mounting torque	Main terminals M6 screw	1.96 ~ 2.94	N·m
		Mounting M6 screw	1.96 ~ 2.94	N·m
		G(E) auxiliary terminal M4 screw	0.98 ~ 1.47	N·m
—	Weight	Typical value	400	g

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

Symbol	Item	Test Conditions	Limits			Unit
			Min	Typ	Max	
I _{CE} S	Collector cutoff current	V _{CE} = V _{CE} S, V _{GE} = 0V	—	—	1	mA
V _{GE(th)}	Gate-emitter threshold voltage	I _C = 60mA, V _{CE} = 10V	3	4	5	V
I _{GE} S	Gate-leakage current	V _{GE} = V _{GE} S, V _{CE} = 0V	—	—	0.5	μA
V _{CE(sat)}	Collector-emitter saturation voltage	T _j = 25°C	—	1.2	1.7	V
		T _j = 150°C	—	1.1	—	
C _{ies}	Input capacitance	V _{CE} = 10V V _{GE} = 0V	—	—	165	nF
C _{oes}	Output capacitance		—	—	7.5	nF
C _{res}	Reverse transfer capacitance		—	—	5.6	nF
Q _G	Total gate charge	V _{CC} = 100V, I _C = 600A, V _{GE} = 10V	—	2200	—	nC
t _{d(on)}	Turn-on delay time	V _{CC} = 100V, I _C = 600A	—	—	1000	ns
t _r	Turn-on rise time	V _{GE1} = V _{GE2} = 10V	—	—	4000	ns
t _{d(off)}	Turn-off delay time	R _G = 4.2Ω	—	—	1000	ns
t _f	Turn-off fall time	Resistive load	—	—	500	ns
V _{EC} (Note 1)	Emitter-collector voltage	I _E = 600A, V _{GE} = 0V	—	—	2.0	V
t _{rr} (Note 1)	Reverse recovery time	I _E = 600A, die / dt = -1200A / μs	—	—	300	ns
Q _{rr} (Note 1)	Reverse recovery charge		—	9.5	—	μC
R _{th(j-c)Q}	Thermal resistance	Junction to case, IGBT part	—	—	0.07	K/W
R _{th(j-c)R}		Junction to case, FWDi part	—	—	0.11	K/W
R _{th(c-f)}	Contact thermal resistance	Case to fin, conductive grease applied	—	—	0.04	K/W

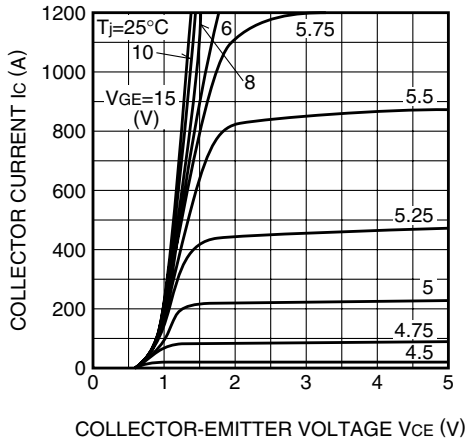
- Note 1. I_E, V_{EC}, t_{rr}, Q_{rr} & die/dt represent characteristics of the anti-parallel, emitter-collector free-wheel diode.
 2. Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.
 3. Junction temperature (T_j) should not increase beyond 150°C.
 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

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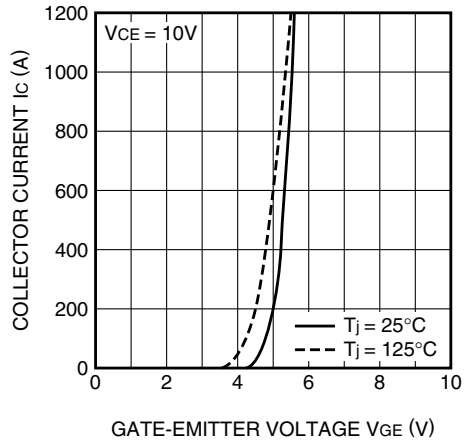
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PERFORMANCE CURVES

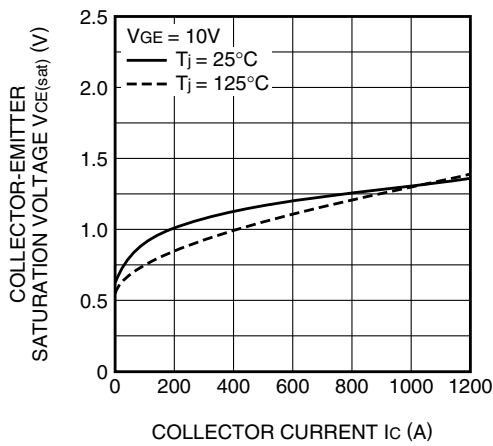
OUTPUT CHARACTERISTICS (TYPICAL)



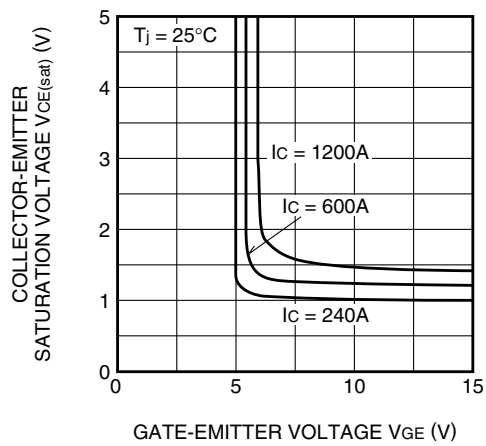
TRANSFER CHARACTERISTICS (TYPICAL)



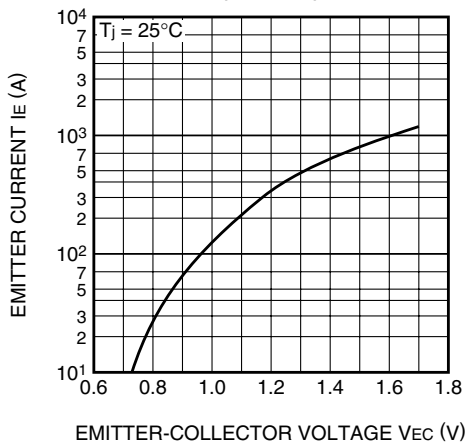
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



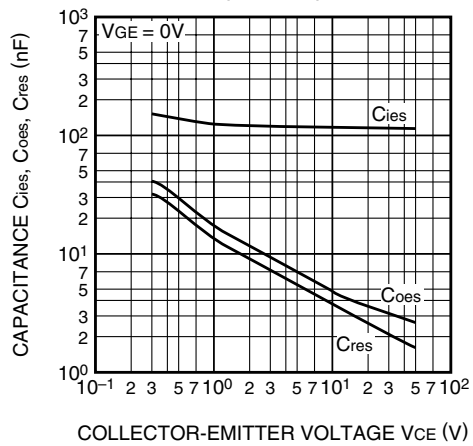
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



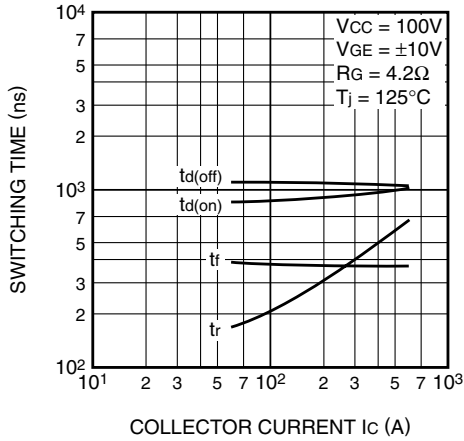
CAPACITANCE CHARACTERISTICS (TYPICAL)



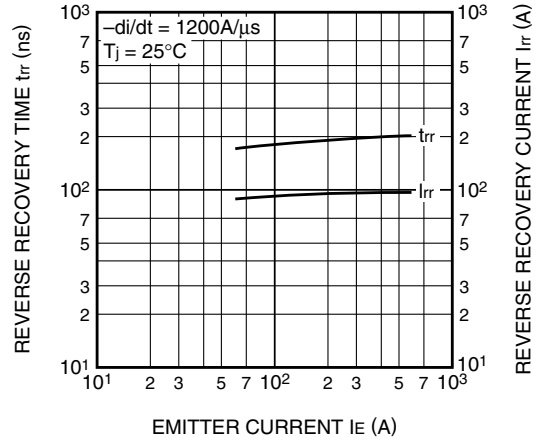
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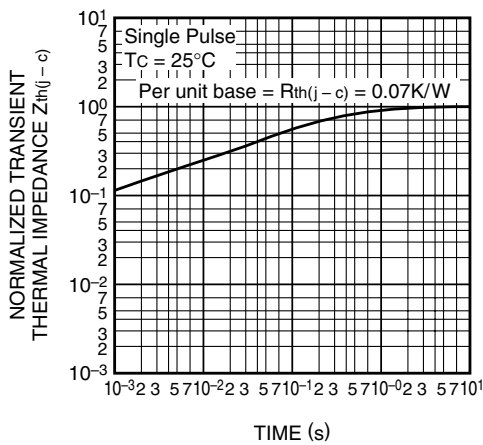
HALF-BRIDGE
SWITCHING TIME CHARACTERISTICS
(TYPICAL)



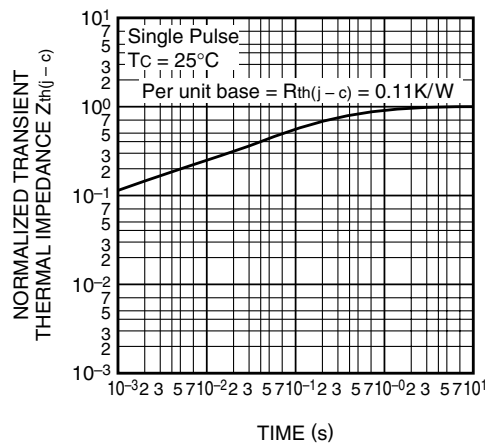
REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi part)



GATE CHARGE CHARACTERISTICS
(TYPICAL)

